

Fig. 1

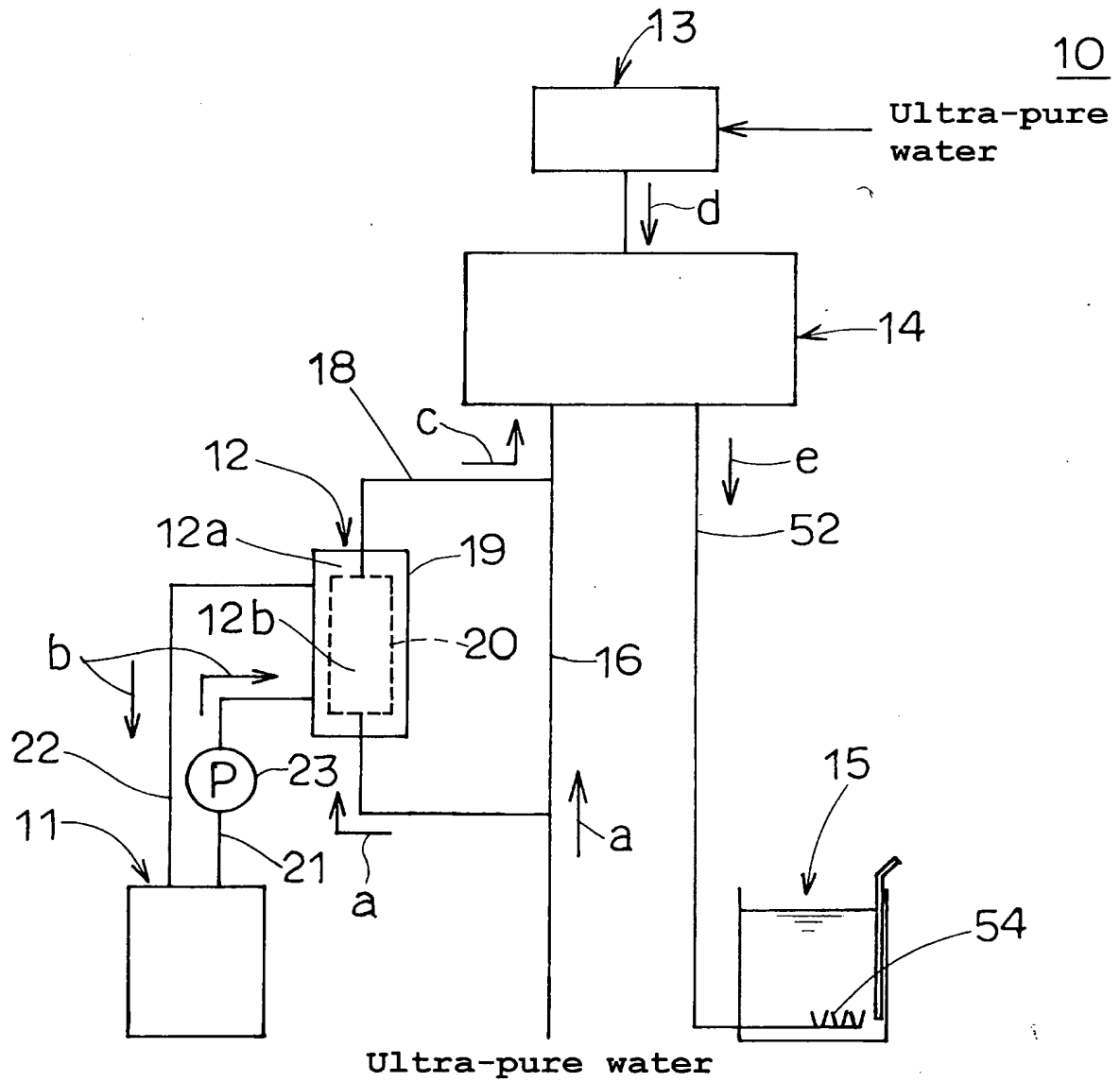
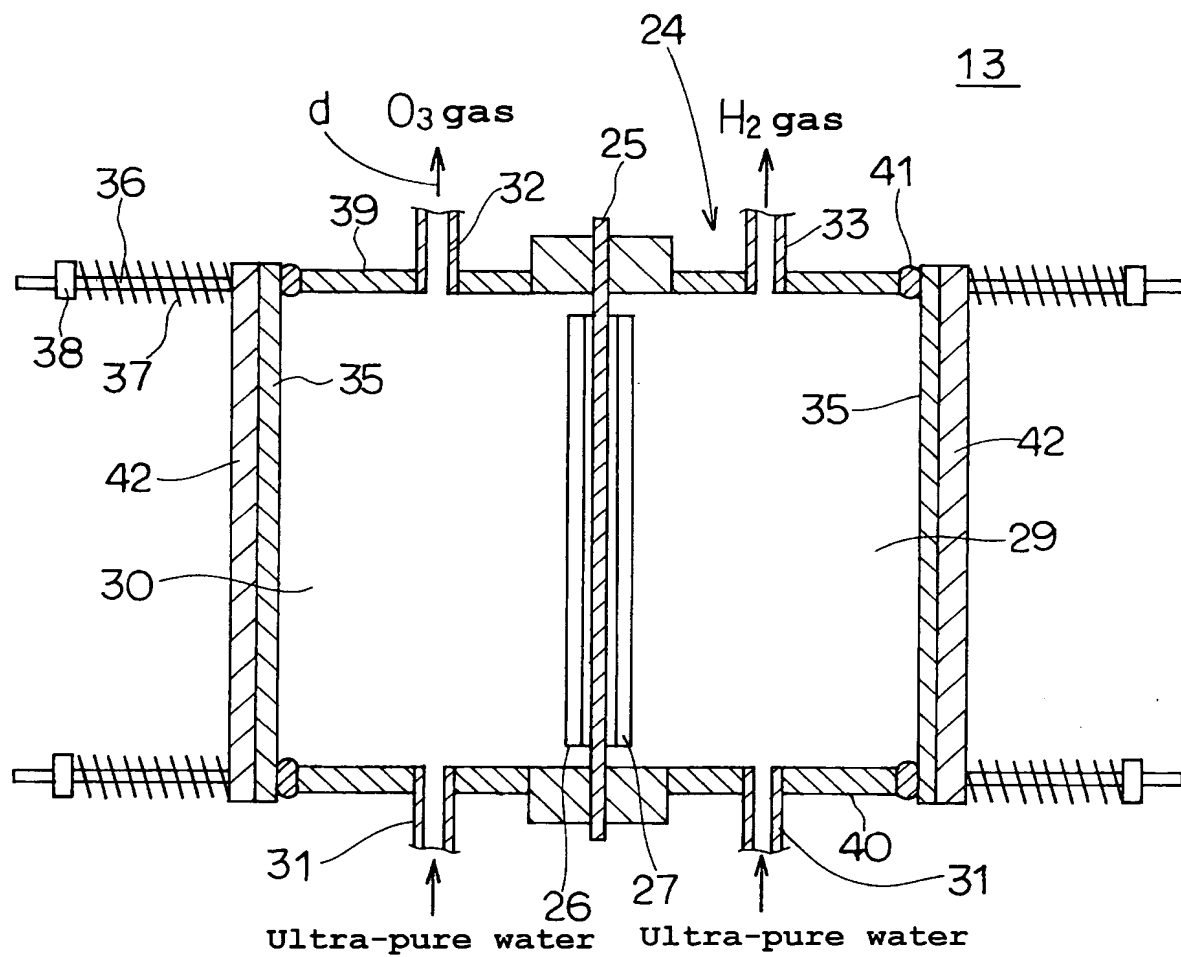


Fig. 2



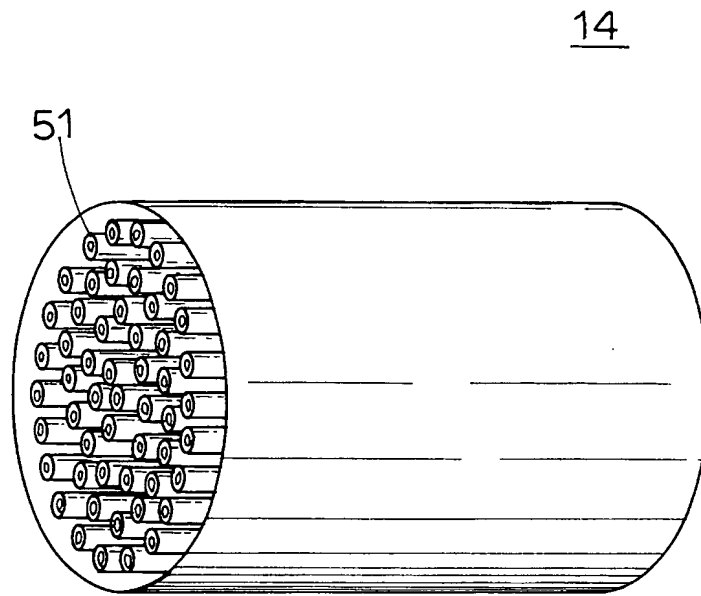
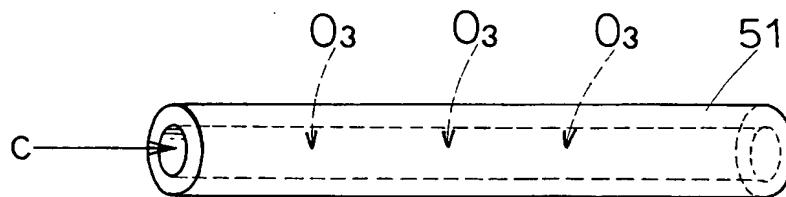
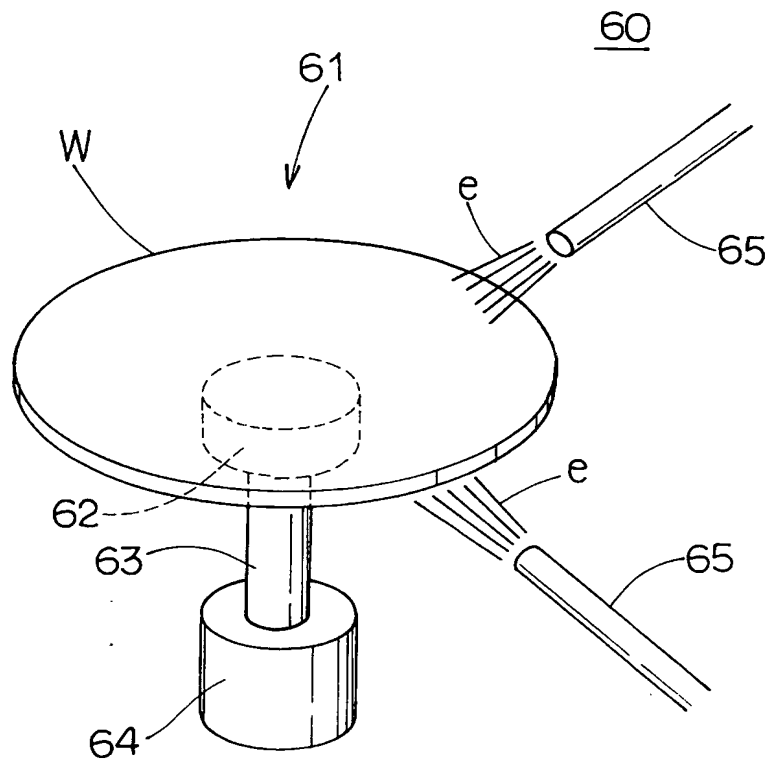
**Fig. 3****Fig. 4**

Fig. 5



A detailed cross-sectional diagram of a semiconductor device 70. The device consists of several stacked layers. At the top is a layer labeled 70A. Below it are layers 71, 72, 73, 74, 75, and 76. A central core or channel is formed by layers 72, 73, and 74. On the left side, there is a U-shaped component 78. Various electrical contacts and gates are indicated: 71a and 71b are contacts at the top; 72a and 72b are contacts at the bottom; 73a is a contact on the right side. Gate structures are labeled S7. A diode-like structure 77 is shown on the right side, connected to layer 75.